

2SK1519, 2SK1520

Silicon N Channel MOS FET

REJ03G0948-0300 (Previous: ADE-208-1288) Rev.3.00 Apr 27, 2006

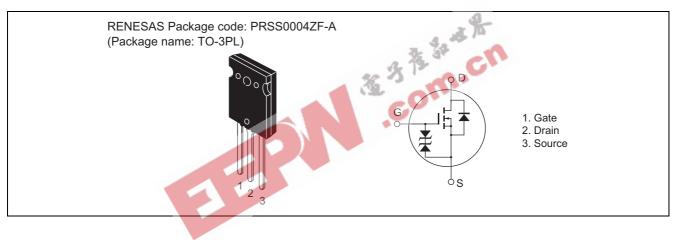
Application

High speed power switching

Features

- Low on-resistance
- High speed switching
- Low drive current
- Built-in fast recovery diode ($t_{rr} = 120 \text{ ns}$)
- Suitable for motor control, switching regulator, DC-DC converter

Outline





Absolute Maximum Ratings

			$(Ta = 25^{\circ}C)$
	Symbol	Ratings	Unit
2SK1519	V _{DSS}	450	V
2SK1520		500	
Gate to source voltage		±30	V
	ID	30	А
	I _{D(pulse)} * ¹	120	А
Body to drain diode reverse drain current		30	А
Channel dissipation		200	W
	Tch	150	°C
	Tstg	-55 to +150	°C
	2SK1520	2SK1519 V _{DSS} 2SK1520 VGSS ID ID ID(pulse)*1 IDR Pch*2 Tch	$\begin{array}{c c c c c c c c c c c c c c c c c c c $

Notes: 1. PW \leq 10 $\mu s,\,duty\,cycle \leq$ 1%

2. Value at $T_C = 25^{\circ}C$

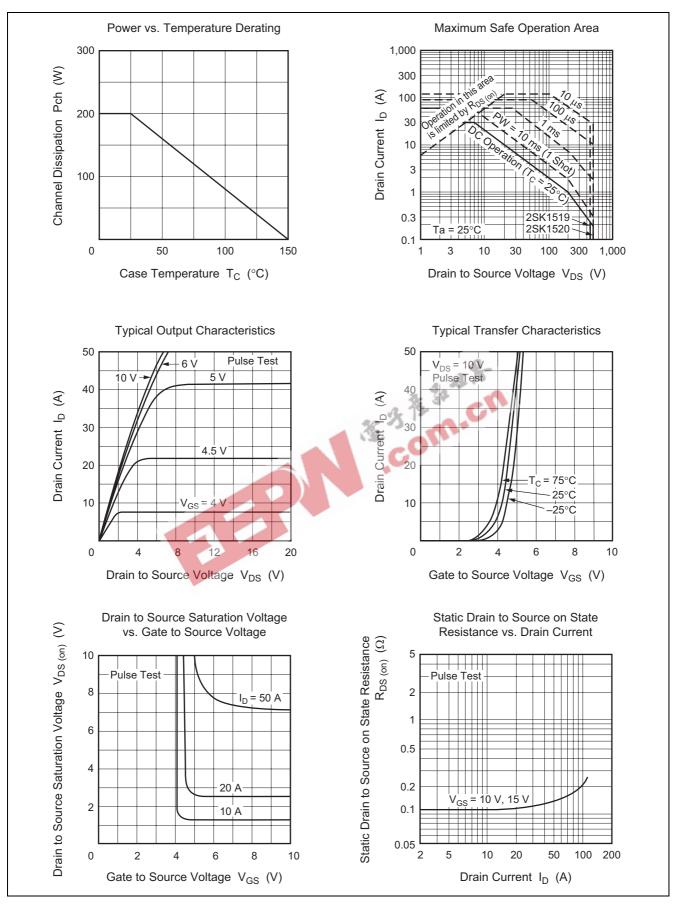
Electrical Characteristics

							$(Ta = 25^{\circ}C)$
Item		Symbol	Min	Тур	Max	Unit	Test conditions
Drain to source	2SK1519	V _{(BR)DSS}	450			V	$I_D = 10 \text{ mA}, V_{GS} = 0$
breakdown voltage	2SK1520		500				
Gate to source breakdown voltage		V _{(BR)GSS}	±30	_	—	- V -	$I_{G} = \pm 100 \ \mu A, \ V_{DS} = 0$
Gate to source leak current		I _{GSS}	—	_	±10	μΑ	$V_{GS} = \pm 25 \text{ V}, V_{DS} = 0$
Zero gate voltage drain	2SK1519	I _{DSS}	_	-	250	μA	$V_{DS} = 360 \text{ V}, \text{ V}_{GS} = 0$
current	2SK1520			26	3		$V_{DS} = 400 \text{ V}, V_{GS} = 0$
Gate to source cutoff vol	tage	V _{GS(off)}	2.0		3.0	V	$I_D = 1 \text{ mA}, V_{DS} = 10 \text{ V}$
Static drain to source on	2SK1519	R _{DS(on)}	-	0.11	0.15	Ω	$I_D = 15 \text{ A}, V_{GS} = 10 \text{ V}^{*3}$
state resistance	2SK1520		\mathcal{H}	0.12	0.16		
Forward transfer admitta	nce	y _{fs}	15	25	_	S	$I_D = 15 \text{ A}, V_{DS} = 10 \text{ V}^{*3}$
Input capacitance		Ciss		5800	_	pF	$V_{DS} = 10 V, V_{GS} = 0,$
Output capacitance		Coss	_	1550	_	pF	f = 1 MHz
Reverse transfer capacit	ance	Crss	—	170	_	pF	
Turn-on delay time		t _{d(on)}	—	65	_	ns	$I_D = 15 \text{ A}, V_{GS} = 10 \text{ V},$
Rise time		tr	—	170	_	ns	$R_L = 2 \Omega$
Turn-off delay time		t _{d(off)}	_	415		ns	
Fall time		t _f	_	200		ns	
Body to drain diode forwa	ard voltage	V _{DF}	—	1.1	—	V	$I_F = 30 \text{ A}, V_{GS} = 0$
Body to drain diode reve time	rse recovery	t _{rr}	_	120	—	ns	I _F = 30 A, V _{GS} = 0, di _F /dt = 100 A/μs

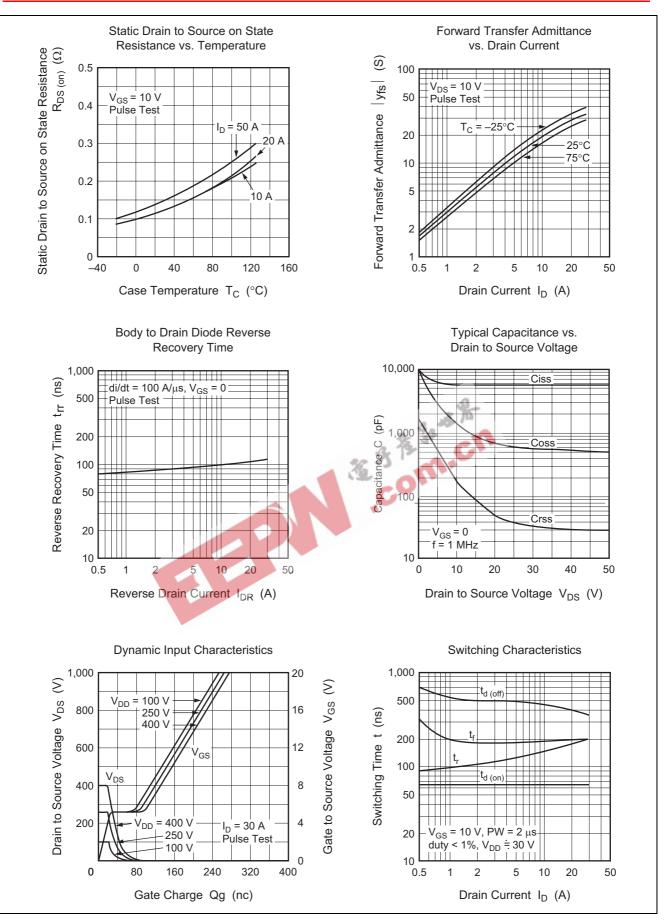
Note: 3. Pulse test



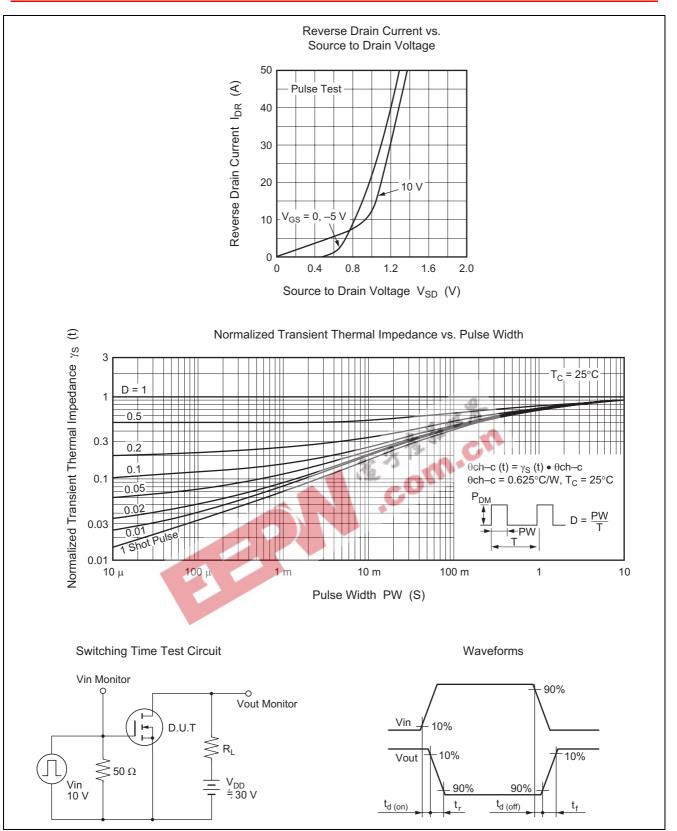
Main Characteristics





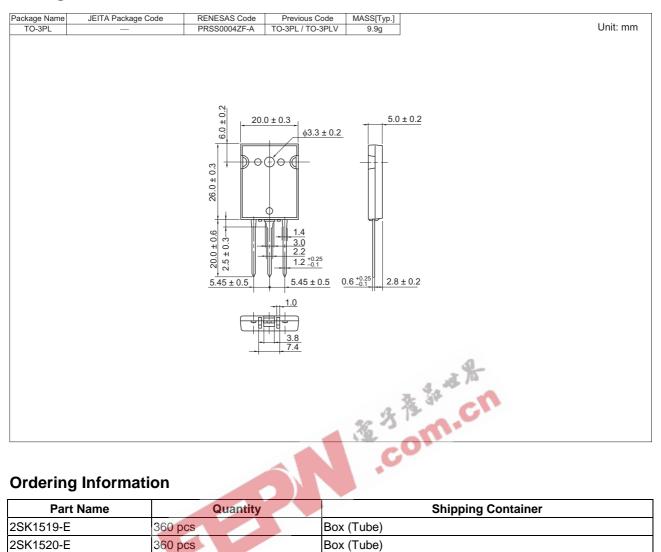








Package Dimensions



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